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TRANSISTORS, HIGH POWER, PNP

BASED ON TYPE 2N5153

ESCC Detail Specification No. 5204/002

Issue 4	September 2009
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DCR No.	CHANGE DESCRIPTION
- 1	Specification up issued to incorporate editorial and technical changes per DCRs.
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1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 <u>APPLICABLE DOCUMENTS</u>

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 <u>The ESCC Component Number</u>

The ESCC Component Number shall be constituted as follows:

Example: 520400201

Detail Specification Reference: 5204002

Component Type Variant Number: 01 (as required)

1.4.2 <u>Component Type Variants</u>

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and Finish	Weight max g
01	2N5153	TO-39	D2	1.5
02	2N5153	TO-39	D3 or D4	1.5
03	2N5153	TO-39	D7	1.5
04	2N5153	TO-257	H2	5
05	2N5153	TO-257	H4	5
06	2N5153	SMD.5	Q14	2
07	2N5153	SMD.5	Q14	2

The lead/terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.



1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	V _{CBO}	-100	V	Over T _{op}
Collector-Emitter Voltage	V _{CEO}	-80	V	Over T _{op} Note 5
Emitter-Base Voltage	V _{EBO}	-5.5	V	Over T _{op}
Collector Current	I _C	-5	А	Continuous Note 5
Power Dissipation For TO-39 For TO-257 and SMD.5	P _{tot1}	1 3.3	w	At T _{amb} ≤ +25°C Note 1
For TO-39 For TO-257 and SMD.5	P _{tot2}	10 35	W	At T _{case} ≤ +25°C Note 1
Thermal Resistance, Junction-to-Ambient For TO-39 For TO-257 and SMD.5	R _{th(j-a)}	175 53	°C/W	
Thermal Resistance, Junction-to-Case For TO-39 For TO-257 and SMD.5	R _{th(j-c)}	17.5 5	°C/W	
Operating Temperature Range	T _{op}	-65 to +200	°C	Note 2
Storage Temperature Range	T _{stg}	-65 to +200	°C	Note 2
Soldering Temperature For TO-39 and TO-257 For SMD.5	T _{sol}	+260 +245	°C	Note 3 Note 4

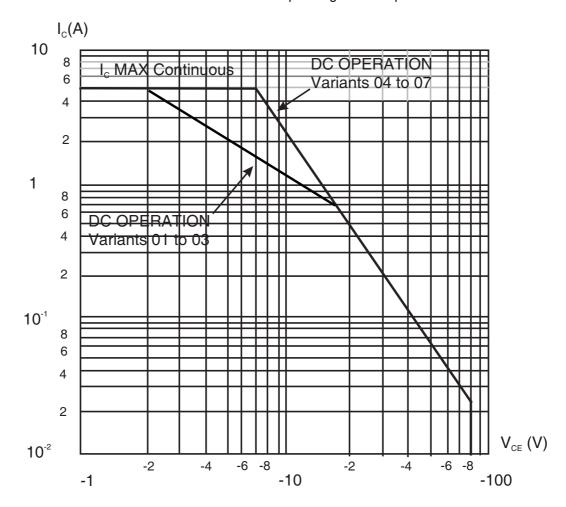
- 1. For T_{amb} or $T_{case} > +25^{\circ}C$, derate linearly to 0W at +200°C.
- 2. For Variants with tin-lead plating or hot solder dip lead finish all testing, and any handling, performed at T_{amb} > +125°C shall be carried out in a 100% inert atmosphere.
- 3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
- 4. Duration 5 seconds maximum and the same package shall not be resoldered until 3 minutes have



elapsed.

5. Safe Operating Area applies as follows:

Maximum Safe Operating Area Graph



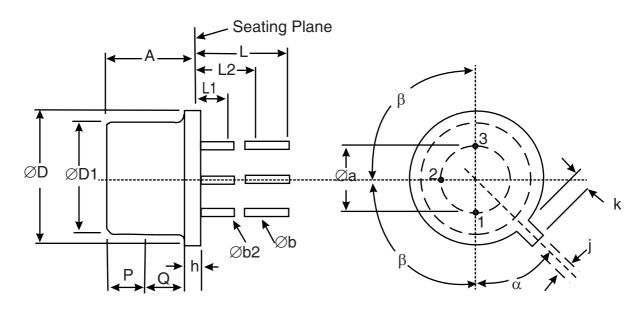
1.6 <u>HANDLING PRECAUTIONS</u>

The TO-257 package contains Beryllium Oxide (BeO) and therefore it must not be ground, machined, sandblasted or subjected to any mechanical operation which will produce dust. The case must not be subjected to any chemical process (e.g. etching) which will produce fumes.



1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.7.1 <u>Metal Can Package (TO-39) - 3 lead</u>



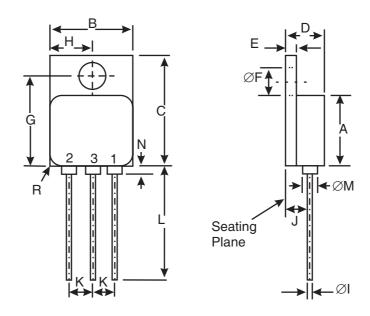
Symbols	Dimensio	Dimensions mm Notes		
Symbols	Min	Max	110163	
Øa	4.83	5.35		
Α	6	6.6		
Øb	0.4	0.533	2, 3	
Øb2	0.4	0.483	2, 3	
ØD	8.31	9.4		
ØD1	ØD1 7.75			
h	0.229	3.18		
j	0.71	0.864		
k	0.737	1.14	4	
L	12.7	19	2	
L1	-	1.27	2, 3	
L2	6.35	-	2, 3	
Р	P 2.54 -		5	
Q	-	-	6	
α	45° E	1, 7		
β	90° E	BSC	1	

- 1. Terminal identification is specified by reference to the tab position where Lead 1 = emitter, Lead 2 = base and Lead 3 = collector.
- 2. Applies to all leads.
- 3. Øb2 applies between L1 and L2. Øb applies between L1 and 12.7mm from the seating plane.



- Diameter is uncontrolled within L1 and beyond 12.7mm from the seating plane.
- 4. Measured from the maximum diameter of the actual device.
- 5. This zone is controlled for automatic handling. The variation in actual diameter within this zone shall not exceed 0.254mm.
- 6. The details of outline in this zone are optional.
- 7. Measured from the tab centreline.

1.7.2 <u>Metal Flange Mount Package (TO-257) - 3 lead</u>



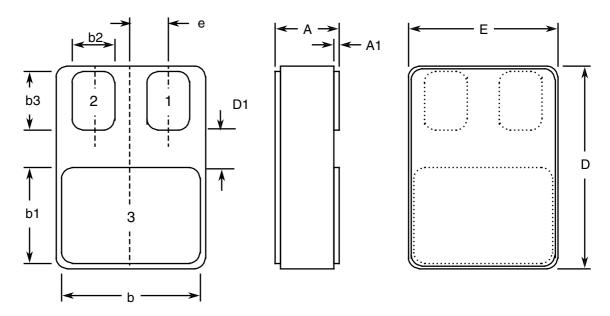
Symbols	Dimensi	Notes	
Symbols	Min	Max	Notes
Α	10.41	10.67	
В	10.41	10.67	
С	16.51	16.76	
D	4.7	5.33	
E	0.89	1.14	
ØF	3.56	3.81	
G	13.39	13.64	
Н	5.13	5.38	
ØI	0.64	0.89	2
J	2.92	3.18	
K	2.41	2.67	
L	15.24	16.51	
ØM	2.29 Typical		2
N	-	0.71	2
R	1.65 T	ypical	3



NOTES:

- 1. Terminal identification is specified by the components geometry where Lead 1 = emitter, Lead 2 = base and Lead 3 = collector.
- 2. Applies to all leads.
- 3. Radius of body corner, 4 places.

1.7.3 <u>Surface Mount Package (SMD.5) - 3 terminal</u>

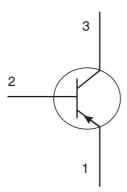


Symbols	Dimension	Notes	
Symbols	Min	Max	Notes
Α	2.84	3.15	
A1	0.25	0.51	
b	7.13	7.39	
b1	5.58	5.84	
b2	2.28	2.54	2
b3	2.92	3.18	2
D	10.03	10.28	
D1	0.76	-	2
E	7.39	7.64	
е	1.91	2	

- 1. Terminal identification is specified by the components geometry where Terminal 1 = emitter (base for Variant 07), Terminal 2 = base (emitter for Variant 07) and Terminal 3 = collector.
- 2. 2 places.

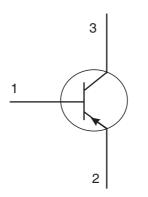


1.8 FUNCTIONAL DIAGRAM



Variants 01 to 06

- 1. Emitter.
- 2. Base.
- 3. Collector.



Variant 07

- 1. Base.
- 2. Emitter.
- Collector.

NOTES:

- 1. For TO-39, the collector is internally connected to the case.
- 2. For TO-257, the case is not connected to any lead.
- 3. For SMD.5, the lid is not connected to any terminal.

1.9 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

a) Case

For the metal can package the case shall be hermetically sealed and have a metal body with hard glass seals.

For the metal flange mount package the case shall be hermetically sealed and have a metal body. The leads pass through ceramic eyelets brazed into the frame and the lid shall be welded.

For the surface mount package the case shall be hermetically sealed and have a ceramic body with a Kovar lid.

b) Leads/Terminals

As specified in Component Type Variants.

2. REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this





specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

2.1.1.1 Deviation from Screening Tests - Chart F3

High Temperature Reverse Bias Burn-in and the subsequent Final Measurements for HTRB shall be omitted.

2.1.1.2 Deviation from Qualification and Periodic Tests - Chart F4

For SMD.5, Terminal Strength is not applicable.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) The ESCC qualified components symbol (for ESCC qualified components only).
- (b) The ESCC Component Number.
- (c) Traceability information.
- (d) Warning sign for Beryllium Oxide (TO-257 only)

2.3 <u>TERMINAL STRENGTH</u>

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

For TO-39, Test Condition: E, lead fatigue.

For TO-257, Test Condition: A, tension, with an applied force of 10N for a duration of 10s.

2.4 <u>VERIFICATION OF SAFE OPERATING AREA</u>

The Safe Operating Area shall be verified as specified in the ESCC Generic Specification and Maximum Ratings herein. The test conditions shall be:

Test Method = MIL-STD-750, Method 3051, Continuous DC

 $T_{case} = +25^{\circ}C$

 $V_{CF} = -18V$

 $I_{C} = -500 \text{mA}$

Operating Time ≤ 50ms



2.5 <u>ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES</u> Electrical measurements shall be performed at room, high and low temperatures.

2.5.1 Room Temperature Electrical Measurements

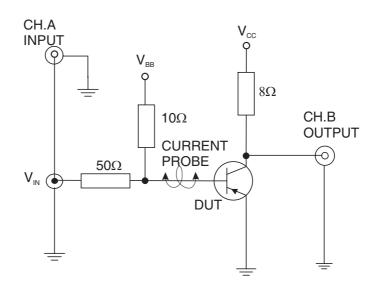
The measurements shall be performed at T_{amb} =+22 ±3°C.

			Test Conditions	Lir	nits	Units	
		Test Method		Min	Max		
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	3011	I _C =-100mA Bias condition D Note 1	-80	-	V	
Collector-Emitter Cut-off Current	I _{CES}	3041	V _{CE} = -60V Bias condition C	-	-1	μΑ	
	I _{CEO}	3041	V _{CE} = -40V Bias condition D	-	-50	μА	
Emitter-Base Cut- off Current	I _{EBO1}	3061	V _{EB} =-4V Bias condition D	-	-1	μΑ	
	I _{EBO2}	3061	V _{EB} =-5.5V Bias condition D	-	-1	mA	
Forward-Current Transfer Ratio	h _{FE1}	3076	V _{CE} =-5V ; I _C = -50mA, Note 1	50	-	-	
	h _{FE2}	3076	V_{CE} =-5V ; I_{C} = -2.5A. Note 1	70	200	-	
	h _{FE3}	3076	V _{CE} =-5V ; I _C =-5A, Note 1	40	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	3071	I _C =-5A I _B =-500mA Note 1, 2	-	-1.5	V	
Base-Emitter Saturation Voltage	V _{BE(sat)1}	3066	I _C =-2.5A I _B =-250mA Test condition A Note 1, 2	-	-1.45	V	
	V _{BE(sat)2}	3066	I _C =-5A I _B =-500mA Test condition A Note 1, 2	-	-2.2	V	
High Frequency Small Signal Current Gain	h _{fe}	3306	V _{CE} =-5V, I _C =-500mA f=20MHz Note 3	3.5	-	-	
Output Capacitance	C _{obo}	3236	V _{CB} =-10V, I _E =0A f=1MHz Note 3	-	250	pF	

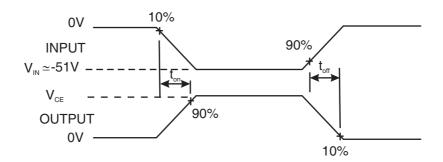


Characteristics	Symbols	MIL-STD-750	Test Conditions	Lin	nits	Units
		Test Method		Min	Max	
Turn-on Time	t _{on}	-	$\begin{tabular}{l} I_{C}=-5A, \\ I_{B1}=-500mA \\ I_{B2}=500mA \\ V_{CC}=-30V \\ V_{BB}=4V \\ V_{IN}\approx-51V \\ Notes \ 3, \ 4 \\ \end{tabular}$	-	500	ns
Turn-off Time	t _{off}	-	$\begin{tabular}{ll} I_{C} = -5A, \\ I_{B1} = -500 mA \\ I_{B2} = 500 mA \\ V_{CC} = -30 V \\ V_{BB} = 4 V \\ V_{IN} \approx -51 V \\ Notes \ 3, \ 4 \\ \end{tabular}$	-	1.3	μs

- 1. Pulse measurement: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
- 2. For TO-39, saturation voltages are measured 6mm from header.
- 3. For AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
- 4. t_{on} and t_{off} shall be measured using the following test circuit. The input waveform shall be supplied by a pulse generator with the following characteristics: $t_r \le 20$ ns, Pulse Width = 10μ s, Duty Cycle = 1%. The sampling oscilloscope for CH.A and CH.B shall have the characteristics $Z_{IN} \ge 100 k\Omega$, $C_{IN} \le 12$ pF and $t_r \le 5$ ns. Adjustment of V_{IN} shall be made with a suitable current probe to achieve the specified I_{B1} and I_{B2} test conditions, where I_{B1} is the on-state base current and I_{B2} is the post off-state base current.







2.5.2 <u>High and Low Temperatures Electrical Measurements</u>

Characteristics	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,		Limits		Units	
		Test Method	Note 1	Min	Max	
Collector-Base Cut-off Current	I _{CES}	3041	T _{amb} =+150(+0-5)°C V _{CE} =-60V, Bias Condition C	-	-10	μА
Forward-Current Transfer Ratio 2	h _{FE2}	3076	T _{amb} =-55(+5-0)°C V _{CE} =-5V I _C =-2.5A Note 2	35	-	-

NOTES:

- 1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
- 2. Pulsed measurement: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

2.6 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols		Units		
		Drift	Abso	olute	
		Value Δ	Min	Max	
					-
Collector-Emitter Cut-off Current	I _{CES}	±100	-	-1000	nA
Forward-Current Transfer Ratio 2	h _{FE2}	±25%	70	200	-
Collector-Emitter Saturation Voltage	V _{CE(sat)}	±100	-	-1500	mV



2.7 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 $\pm 3^{o}$ C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Collector-Emitter Cut-off Current	I _{CES}	-	-1	μΑ
Forward-Current Transfer Ratio 2	h _{FE2}	70	200	-
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	-1.5	V

2.8 <u>HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS</u>

Characteristics	Symbols	Conditions	Units
Ambient Temperature	T _{amb}	+150	°C
Emitter-Base Voltage	V _{EB}	-4.5	V
Collector-Base Voltage	V _{CB}	-60	V
Duration	t	48	hours

2.9 <u>POWER BURN-IN CONDITIONS</u>

2.9.1 <u>Power Burn-in Conditions (TO-39)</u>

Characteristics	Symbols	Conditions	Units
Ambient Temperature	T _{amb}	+20 to +50 (1)	°C
Power Dissipation	P _{tot}	As per Maximum Ratings. Derate P_{tot1} at the chosen T_{amb} using the specified $R_{th(j-a)}$.	W
Collector-Base Voltage	V _{CB}	-20	V

NOTES:

1. No heat sink nor forced air directly on the device shall be permitted.

2.9.2 <u>Power Burn-in Conditions (TO-257 and SMD.5)</u>

Characteristics	Symbols	Conditions	Units
Case Temperature	T _{case}	+100(+0 -5)	°C
Power Dissipation	P _{tot}	As per Maximum Ratings. Derate P_{tot2} at the specified T_{case} using the specified $R_{th(j-c)}$.	W



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Characteristics	Symbols	Conditions	Units
Case Temperature	T _{case}	+100(+0 -5)	°C
Collector-Base Voltage	V _{CB}	-20	V

2.10 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.



APPENDIX 'A'

AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Deviations from Room Temperature Electrical Measurements	All AC characteristics (Room Temperature Electrical Measurement Note 2) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.
Deviations from High and Low Temperatures Electrical Measurements	All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.
Deviations from Screening Tests - Chart F3	Solderability is not applicable unless specifically stipulated in the Purchase Order.